Docket No.: EMCORE 3.0-081
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Guo et al.

Application No.: 10/721,488

Group Art Unit: N/A

Filed: November 25, 2003

Examiner: Not Yet Assigned

For: GALLIUM NITRIDE-BASED DEVICES AND MANUFACTURING PROCESS

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

It is respectfully requested that the references listed on the enclosed form be made of record and considered with respect to the above-referenced U.S. patent application. A copy of each non-U.S. patent reference is enclosed. Submission of the present Information Disclosure Statement should not be taken as an admission that the cited references are legally available prior art or that the same are pertinent or material.

In the event that any fee is due in connection with the present Information Disclosure Statement, the Commissioner is hereby authorized to charge the same to our Deposit Account No. 12-1095.

Dated: December 24, 2003

Respectfully submitted,

By _____

Lawrence E. Russ
Registration No.: 35,342
LERNER, DAVID, LITTENBERG,
KRUMHOLZ & MENTLIK, LLP
600 South Avenue West
Westfield, New Jersey 07090
(908) 654-5000
Attorney for Applicant

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 1 of 2

Complete if Known	
Application Number	10/721,488
Filing Date	November 25, 2003
First Named Inventor	Shiping Guo
Art Unit	N/A
Examiner Name	Not Yet Assigned
Attorney Docket Number	EMCORE 3.0-081

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	BB	-DE 4210402	10-01-1992	Koichi		
	BC	-EP 0 380 340	04-29-1992	Cree Research Inc.		

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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
	CA	Brown, et al., "AlGaN/GaN HFETs Fabricated on 100-mm GaN on Silicon (111) Substrates," Solid-State Electronics, Vol. 46, pp. 1535-1539 (2002)	
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	CD	Armitage, et al., "Lattice-Matched HfN Buffer Layers for Epitaxy of GaN on Si," Applied	

Examiner Signature		Date Considered	

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		Physics Letters, Vol. 81, No. 8, pp. 1450-1452 (August 15, 2002)	
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